Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	1232
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	72
Number of Gates	8000
Voltage - Supply	4.5V ~ 5.5V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	84-LCC (J-Lead)
Supplier Device Package	84-PLCC (29.31x29.31)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/a1280a-1plg84i

Product Plan

Device/Package	Speed Grade[1]			Application[1]			
	Std.	–1	–2	C	I	M	B
A1225A Device							
84-Pin Plastic Leaded Chip Carrier (PL)	✓	✓	✓	✓	✓	–	–
100-Pin Plastic Quad Flatpack (PQ)	✓	✓	✓	✓	✓	–	–
100-Pin Very Thin Quad Flatpack (VQ)	✓	✓	✓	✓	–	–	–
100-Pin Ceramic Pin Grid Array (PG)	✓	✓	✓	✓	–	–	–
A1240A Device							
84-Pin Plastic Leaded Chip Carrier (PL)	✓	✓	✓	✓	✓	–	–
132-Pin Ceramic Pin Grid Array (PG)	✓	✓	✓	✓	–	✓	✓
144-Pin Plastic Quad Flat Pack (PQ)	✓	✓	✓	✓	✓	–	–
176-Pin Thin (1.4 mm) Quad Flat Pack (TQ)	✓	✓	✓	✓	–	–	–
A1280A Device							
160-Pin Plastic Quad Flatpack (PQ)	✓	✓	✓	✓	✓	–	–
172-Pin Ceramic Quad Flatpack (CQ)	✓	✓	✓	✓	–	✓	✓
176-Pin Ceramic Pin Grid Array (PG)	✓	✓	✓	✓	–	✓	✓
176-Pin Thin (1.4 mm) Quad Flat Pack (TQ)	✓	✓	✓	✓	–	–	–

Notes:

1. *Applications:*
   C = Commercial
   I = Industrial
   M = Military
   B = MIL-STD-883

Availability:
✓ = Available
P = Planned
– = Not planned

Speed Grade:
–1 = Approx. 15% faster than Std.
–2 = Approx. 25% faster than Std.

2. *Contact your Microsemi SoC Products Group sales representative for product availability.*

Device Resources

Device Series	Logic Modules	Gates	User I/Os									
			PG176	PG132	PG100	PQ160	PQ144	PQ100	PL84	CQ172	TQ176	VQ100
A1225A	451	2,500	–	–	83	–	–	83	72	–	–	83
A1240A	684	4,000	–	104	–	–	104	–	72	–	104	–
A1280A	1,232	8,000	140	–	–	125	–	–	72	140	140	–

Contact your local Microsemi SoC Products Group representative for device availability:
http://www.microsemi.com/soc/contact/default.aspx.

Table of Contents

Table 2-3 • Electrical Specifications

Symbol	Parameter	Commercial		Industrial		Military		Units
		Min.	Max.	Min.	Max.	Min.	Max.	
VOH[1]	(IOH = –10 mA)[2]	2.4	–	–	–	–	–	V
	(IOH = –6 mA)	3.84	–	–	–	–	–	V
	(IOH = –4 mA)	–	–	3.7	–	3.7	–	V
VOL[1]	(IOL = 10 mA)[2]	–	0.5	–	–	–	–	V
	(IOL = 6 mA)	–	0.33	–	0.40	–	0.40	V
VIL		–0.3	0.8	–0.3	0.8	–0.3	0.8	V
VIH		2.0	VCC + 0.3	2.0	VCC + 0.3	2.0	VCC + 0.3	V
Input Transition Time t_R, t_F[2]		–	500	–	500	–	500	ns
C_{IO} I/O capacitance[2,3]		–	10	–	10	–	10	pF
Standby Current, ICC[4] (typical = 1 mA)		–	2	–	10	–	20	mA
Leakage Current[5]		–10	+10	–10	+10	–10	+10	µA
ICC(D)	Dynamic VCC supply current. See the Power Dissipation section.							

Notes:

1. *Only one output tested at a time. VCC = minimum.*
2. *Not tested, for information only.*
3. *Includes worst-case PG176 package capacitance. VOUT = 0 V, f = 1 MHz*
4. *All outputs unloaded. All inputs = VCC or GND, typical ICC = 1 mA. ICC limit includes IPP and ISV during normal operations.*
5. *VOUT, VIN = VCC or GND.*

Package Thermal Characteristics

The device junction to case thermal characteristic is θjc, and the junction to ambient air characteristic is θja. The thermal characteristics for θja are shown with two different air flow rates.

Maximum junction temperature is 150°C.

A sample calculation of the absolute maximum power dissipation allowed for a PQ160 package at commercial temperature and still air is as follows:

$$\frac{\text{Max. junction temp. (°C)} - \text{Max. ambient temp. (°C)}}{\theta_{ja}\text{°C/W}} = \frac{150\text{°C} - 70\text{°C}}{33\text{°C/W}} = 2.4\text{ W}$$

EQ 1

Table 2-4 • **Package Thermal Characteristics**

Package Type*	Pin Count	θ_{jc}	θ_{ja} Still Air	θ_{ja} 300 ft./min.	Units
Ceramic Pin Grid Array	100	5	35	17	°C/W
	132	5	30	15	°C/W
	176	8	23	12	°C/W
Ceramic Quad Flatpack	172	8	25	15	°C/W
Plastic Quad Flatpack[1]	100	13	48	40	°C/W
	144	15	40	32	°C/W
	160	15	38	30	°C/W
Plastic Leaded Chip Carrier	84	12	37	28	°C/W
Very Thin Quad Flatpack	100	12	43	35	°C/W
Thin Quad Flatpack	176	15	32	25	°C/W

Notes: (Maximum Power in Still Air)

1. *Maximum power dissipation values for PQFP packages are 1.9 W (PQ100), 2.3 W (PQ144), and 2.4 W (PQ160).*
2. *Maximum power dissipation for PLCC packages is 2.7 W.*
3. *Maximum power dissipation for VQFP packages is 2.3 W.*
4. *Maximum power dissipation for TQFP packages is 3.1 W.*

Power Dissipation

P = [ICC standby + ICCactive] * VCC + IOL * VOL * N + IOH* (VCC – VOH) * M

EQ 2

where:

ICC standby is the current flowing when no inputs or outputs are changing

ICCactive is the current flowing due to CMOS switching.

IOL and IOH are TTL sink/source currents.

VOL and VOH are TTL level output voltages.

N is the number of outputs driving TTL loads to VOL.

M is the number of outputs driving TTL loads to VOH.

An accurate determination of N and M is problematical because their values depend on the family type, design details, and on the system I/O. The power can be divided into two components: static and active.

Static Power Component

Microsemi FPGAs have small static power components that result in lower power dissipation than PALs or PLDs. By integrating multiple PALs/PLDs into one FPGA, an even greater reduction in board-level power dissipation can be achieved.

The power due to standby current is typically a small component of the overall power. Standby power is calculated in Table 2-5 for commercial, worst case conditions.

Table 2-5 **• Standby Power Calculation**

ICC	VCC	Power
2 mA	5.25 V	10.5 mW

The static power dissipated by TTL loads depends on the number of outputs driving high or low and the DC load current. Again, this value is typically small. For instance, a 32-bit bus sinking 4 mA at 0.33 V will generate 42 mW with all outputs driving low, and 140 mW with all outputs driving high. The actual dissipation will average somewhere between as I/Os switch states with time.

Active Power Component

Power dissipation in CMOS devices is usually dominated by the active (dynamic) power dissipation. This component is frequency dependent, a function of the logic and the external I/O. Active power dissipation results from charging internal chip capacitances of the interconnect, unprogrammed antifuses, module inputs, and module outputs, plus external capacitance due to PC board traces and load device inputs.

An additional component of the active power dissipation is the totem-pole current in CMOS transistor pairs. The net effect can be associated with an equivalent capacitance that can be combined with frequency and voltage to represent active power dissipation.

Equivalent Capacitance

The power dissipated by a CMOS circuit can be expressed by EQ 3.

$$\text{Power } (\mu W) = C_{EQ} * VCC^2 * F$$

EQ 3

Where:

C_{EQ} is the equivalent capacitance expressed in pF.

VCC is the power supply in volts.

F is the switching frequency in MHz.

Equivalent capacitance is calculated by measuring ICC active at a specified frequency and voltage for each circuit component of interest. Measurements have been made over a range of frequencies at a fixed value of VCC. Equivalent capacitance is frequency independent so that the results may be used over a wide range of operating conditions. Equivalent capacitance values are shown in Table 2-6.

Table 2-6 **• CEQ Values for Microsemi FPGAs**

Item	CEQ Value
Modules (C_{EQM})	5.8
Input Buffers (C_{EQI})	12.9
Output Buffers (C_{EQO})	23.8
Routed Array Clock Buffer Loads (C_{EQCR})	3.9

Parameter Measurement

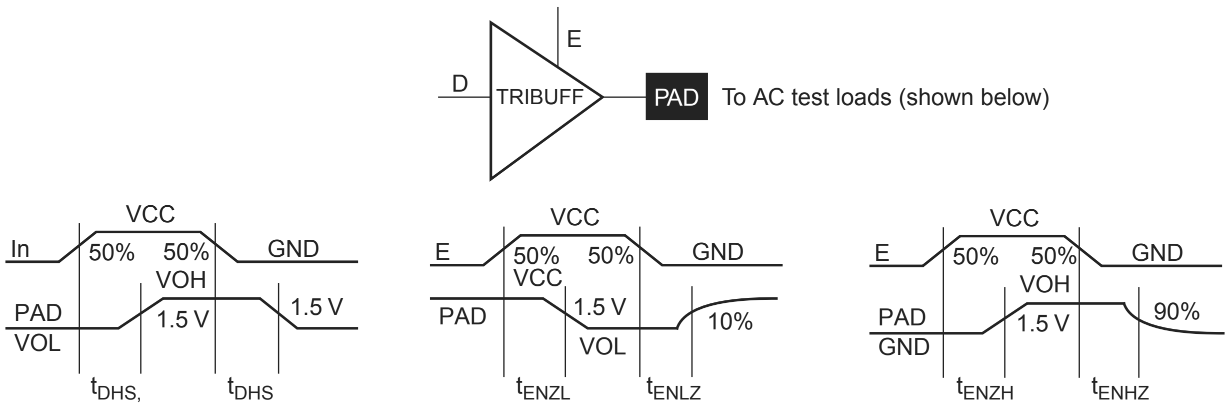


Figure 2-2 • **Output Buffer Delays**

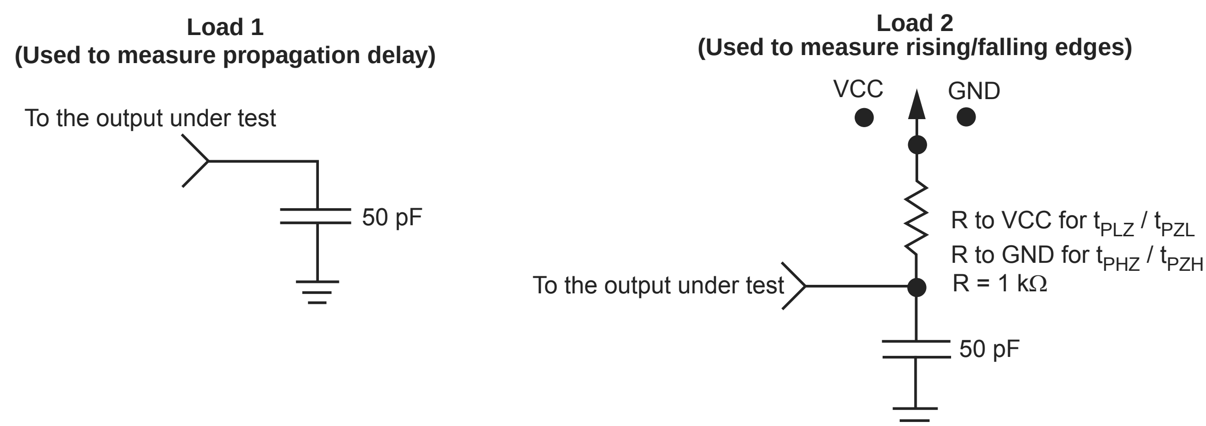


Figure 2-3 • **AC Test Loads**

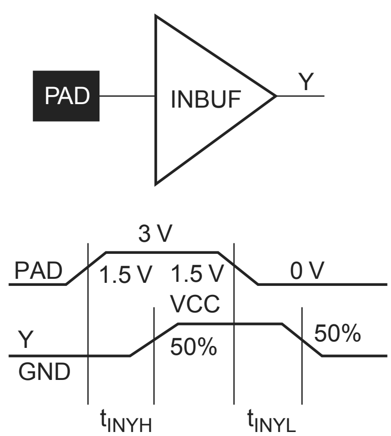


Figure 2-4 • **Input Buffer Delays**

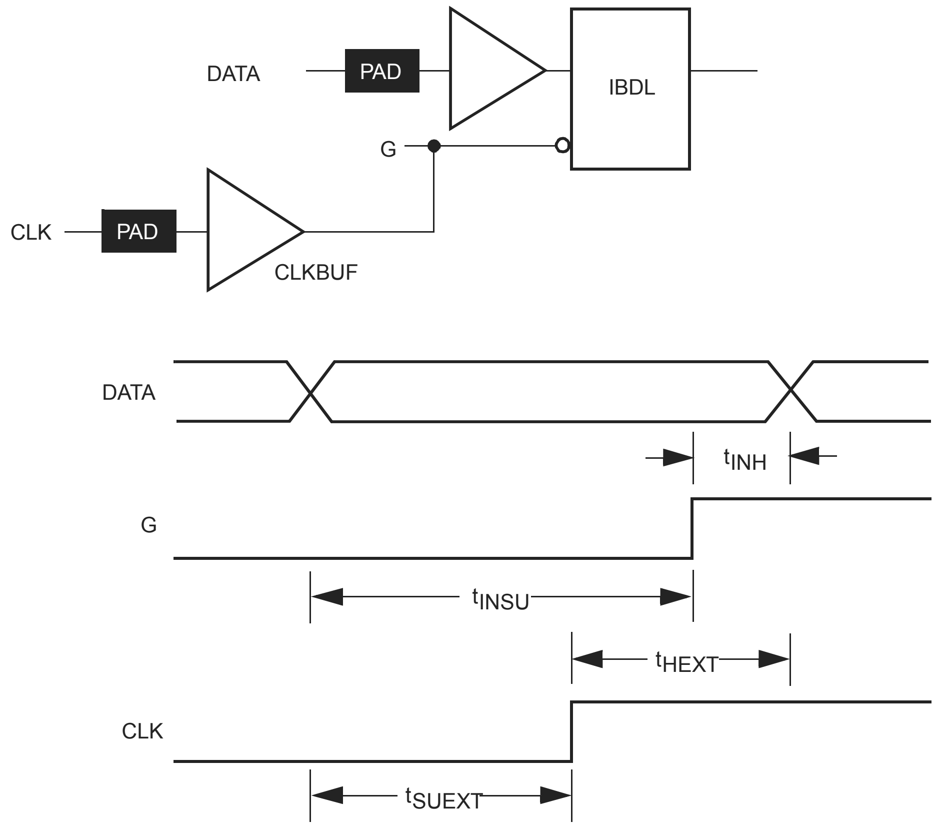


Figure 2-7 • **Input Buffer Latches**

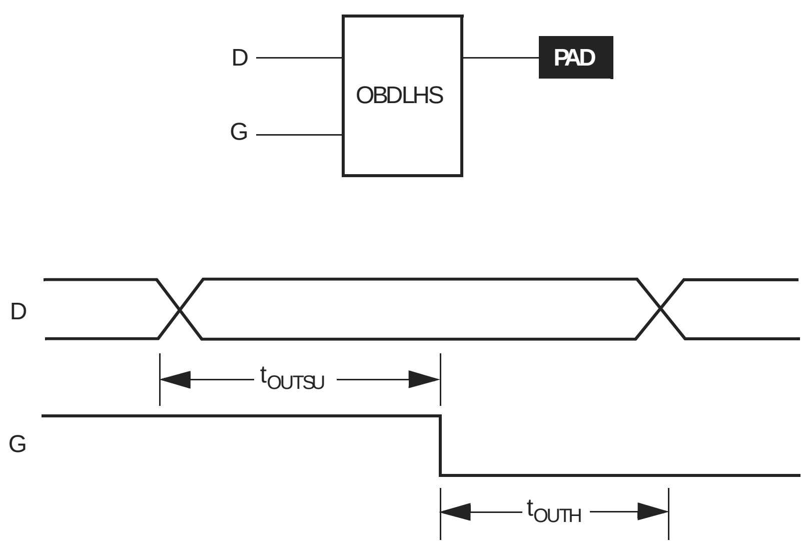


Figure 2-8 • **Output Buffer Latches**

Timing Derating Factor (Temperature and Voltage)

Table 2-9 • **Timing Derating Factor (Temperature and Voltage)**

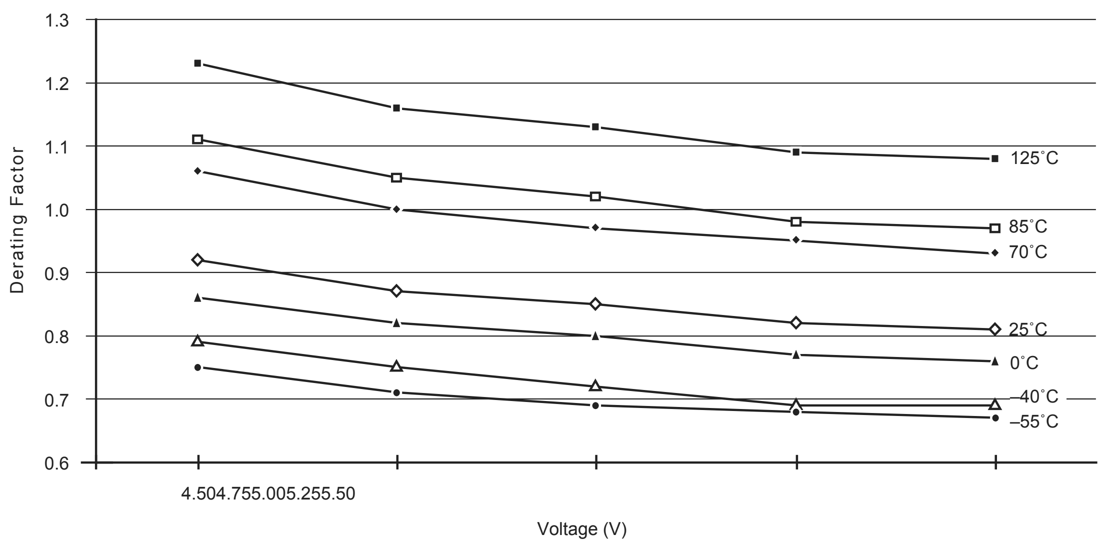
(Commercial Minimum/Maximum Specification) x	Industrial		Military	
	Min.	**Max.**	**Min.**	Max.
	0.69	1.11	0.67	1.23

Table 2-10 • **Timing Derating Factor for Designs at Typical Temperature (T_J = 25°C) and Voltage (5.0 V)**

(Commercial Maximum Specification) x	0.85

Table 2-11 • **Temperature and Voltage Derating Factors (normalized to Worst-Case Commercial, TJ = 4.75 V, 70°C)**

	–55	**–40**	**0**	**25**	**70**	**85**	**125**
4.50	0.75	0.79	0.86	0.92	1.06	1.11	1.23
4.75	0.71	0.75	0.82	0.87	1.00	1.05	1.13
5.00	0.69	0.72	0.80	0.85	0.97	1.02	1.13
5.25	0.68	0.69	0.77	0.82	0.95	0.98	1.09
5.50	0.67	0.69	0.76	0.81	0.93	0.97	1.08



Note: This derating factor applies to all routing and propagation delays.

Figure 2-9 • **Junction Temperature and Voltage Derating Curves (normalized to Worst-Case Commercial, T_J = 4.75 V, 70°C)**

A1225A Timing Characteristics (continued)

Table 2-13 **• A1225A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C**

I/O Module Input Propagation Delays			–2 Speed		–1 Speed		Std. Speed		Units
Parameter/Description			Min.	Max.	Min.	Max.	Min.	Max.	
t_{INYH}	Pad to Y High			2.9		3.3		3.8	ns
t_{INYL}	Pad to Y Low			2.6		3.0		3.5	ns
t_{INGH}	G to Y High			5.0		5.7		6.6	ns
t_{INGL}	G to Y Low			4.7		5.4		6.3	ns
Input Module Predicted Input Routing Delays*									
t_{IRD1}	FO = 1 Routing Delay			4.1		4.6		5.4	ns
t_{IRD2}	FO = 2 Routing Delay			4.6		5.2		6.1	ns
t_{IRD3}	FO = 3 Routing Delay			5.3		6.0		7.1	ns
t_{IRD4}	FO = 4 Routing Delay			5.7		6.4		7.6	ns
t_{IRD8}	FO = 8 Routing Delay			7.4		8.3		9.8	ns
Global Clock Network									
t_{CKH}	Input Low to High	FO = 32		10.2		11.0		12.8	ns
		FO = 256		11.8		13.0		15.7	
t_{CKL}	Input High to Low	FO = 32		10.2		11.0		12.8	ns
		FO = 256		12.0		13.2		15.9	
t_{PWH}	Minimum Pulse Width High	FO = 32	3.4		4.1		4.5		ns
		FO = 256	3.8		4.5		5.0		
t_{PWL}	Minimum Pulse Width Low	FO = 32	3.4		4.1		4.5		ns
		FO = 256	3.8		4.5		5.0		
t_{CKSW}	Maximum Skew	FO = 32		0.7		0.7		0.7	ns
		FO = 256		3.5		3.5		3.5	
t_{SUEXT}	Input Latch External Setup	FO = 32	0.0		0.0		0.0		ns
		FO = 256	0.0		0.0		0.0		
t_{HEXT}	Input Latch External Hold	FO = 32	7.0		7.0		7.0		ns
		FO = 256	11.2		11.2		11.2		
t_P	Minimum Period	FO = 32	7.7		8.3		9.1		ns
		FO = 256	8.1		8.8		10.0		
f_{MAX}	Maximum Frequency	FO = 32		130.0		120.0		110.0	ns
		FO = 256		125.0		115.0		100.0	

*Note: *These parameters should be used for estimating device performance. Optimization techniques may further reduce delays by 0 to 4 ns. Routing delays are for typical designs across worst-case operating conditions. Post-route timing analysis or simulation is required to determine actual worst-case performance. Post-route timing is based on actual routing delay measurements performed on the device prior to shipment.*

A1280A Timing Characteristics

Table 2-18 **• A1280A Worst-Case Commercial Conditions, VCC = 4.75 V, T_J = 70°C**

Logic Module Propagation Delays[1]		–2 Speed[3]		–1 Speed		Std. Speed		Units
Parameter/Description		Min.	Max.	Min.	Max.	Min.	Max.	
t_{PD1}	Single Module		3.8		4.3		5.0	ns
t_{CO}	Sequential Clock to Q		3.8		4.3		5.0	ns
t_{GO}	Latch G to Q		3.8		4.3		5.0	ns
t_{RS}	Flip-Flop (Latch) Reset to Q		3.8		4.3		5.0	ns
Predicted Routing Delays[2]								
t_{RD1}	FO = 1 Routing Delay		1.7		2.0		2.3	ns
t_{RD2}	FO = 2 Routing Delay		2.5		2.8		3.3	ns
t_{RD3}	FO = 3 Routing Delay		3.0		3.4		4.0	ns
t_{RD4}	FO = 4 Routing Delay		3.7		4.2		4.9	ns
t_{RD8}	FO = 8 Routing Delay		6.7		7.5		8.8	ns
Sequential Timing Characteristics[3,4]								
t_{SUD}	Flip-Flop (Latch) Data Input Setup	0.4		0.4		0.5		ns
t_{HD}	Flip-Flop (Latch) Data Input Hold	0.0		0.0		0.0		ns
t_{SUENA}	Flip-Flop (Latch) Enable Setup	0.8		0.9		1.0		ns
t_{HENA}	Flip-Flop (Latch) Enable Hold	0.0		0.0		0.0		ns
t_{WCLKA}	Flip-Flop (Latch) Clock Active Pulse Width	5.5		6.0		7.0		ns
t_{WASYN}	Flip-Flop (Latch) Clock Asynchronous Pulse Width	5.5		6.0		7.0		ns
t_A	Flip-Flop Clock Input Period	11.7		13.3		18.0		ns
t_{INH}	Input Buffer Latch Hold	0.0		0.0		0.0		ns
t_{INSU}	Input Buffer Latch Setup	0.4		0.4		0.5		ns
t_{OUTH}	Output Buffer Latch Hold	0.0		0.0		0.0		ns
t_{OUTSU}	Output Buffer Latch Setup	0.4		0.4		0.5		ns
f_{MAX}	Flip-Flop (Latch) Clock Frequency		85.0		75.0		50.0	MHz

Notes:

1. *For dual-module macros, use $t_{PD1} + t_{RD1} + t_{PDn}$, $t_{CO} + t_{RD1} + t_{PDn}$, or $t_{PD1} + t_{RD1} + t_{SUD}$—whichever is appropriate.*
2. *Routing delays are for typical designs across worst-case operating conditions. These parameters should be used for estimating device performance. Post-route timing analysis or simulation is required to determine actual worst-case performance. Post-route timing is based on actual routing delay measurements performed on the device prior to shipment.*
3. *Data applies to macros based on the S-module. Timing parameters for sequential macros constructed from C-modules can be obtained from the DirectTime Analyzer utility.*
4. *Setup and hold timing parameters for the Input Buffer Latch are defined with respect to the PAD and the D input. External setup/hold timing parameters must account for delay from an external PAD signal to the G inputs. Delay from an external PAD signal to the G input subtracts (adds) to the internal setup (hold) time.*

Pin Descriptions

CLKA Clock A (Input)

TTL Clock input for clock distribution networks. The Clock input is buffered prior to clocking the logic modules. This pin can also be used as an I/O.

CLKB Clock B (Input)

TTL Clock input for clock distribution networks. The Clock input is buffered prior to clocking the logic modules. This pin can also be used as an I/O.

DCLK Diagnostic Clock (Input)

TTL Clock input for diagnostic probe and device programming. DCLK is active when the MODE pin is High. This pin functions as an I/O when the MODE pin is Low.

GND Ground

Low supply voltage.

I/O Input/Output (Input, Output)

The I/O pin functions as an input, output, three-state, or bidirectional buffer. Input and output levels are compatible with standard TTL and CMOS specifications. Unused I/O pins are automatically driven Low by the ALS software.

MODE Mode (Input)

The MODE pin controls the use of multifunction pins (DCLK, PRA, PRB, SDI). When the MODE pin is High, the special functions are active. When the MODE pin is Low, the pins function as I/Os. To provide Actionprobe capability, the MODE pin should be terminated to GND through a 10K resistor so that the MODE pin can be pulled High when required.

NC No Connection

This pin is not connected to circuitry within the device.

PRA Probe A (Output)

The Probe A pin is used to output data from any user-defined design node within the device. This independent diagnostic pin can be used in conjunction with the Probe B pin to allow real-time diagnostic output of any signal path within the device. The Probe A pin can be used as a user-defined I/O when debugging has been completed. The pin’s probe capabilities can be permanently disabled to protect programmed design confidentiality. PRA is active when the MODE pin is High. This pin functions as an I/O when the MODE pin is Low.

PRB Probe B (Output)

The Probe B pin is used to output data from any user-defined design node within the device. This independent diagnostic pin can be used in conjunction with the Probe A pin to allow real-time diagnostic output of any signal path within the device. The Probe B pin can be used as a user-defined I/O when debugging has been completed. The pin’s probe capabilities can be permanently disabled to protect programmed design confidentiality. PRB is active when the MODE pin is High. This pin functions as an I/O when the MODE pin is Low.

SDI Serial Data Input (Input)

Serial data input for diagnostic probe and device programming. SDI is active when the MODE pin is High. This pin functions as an I/O when the MODE pin is Low.

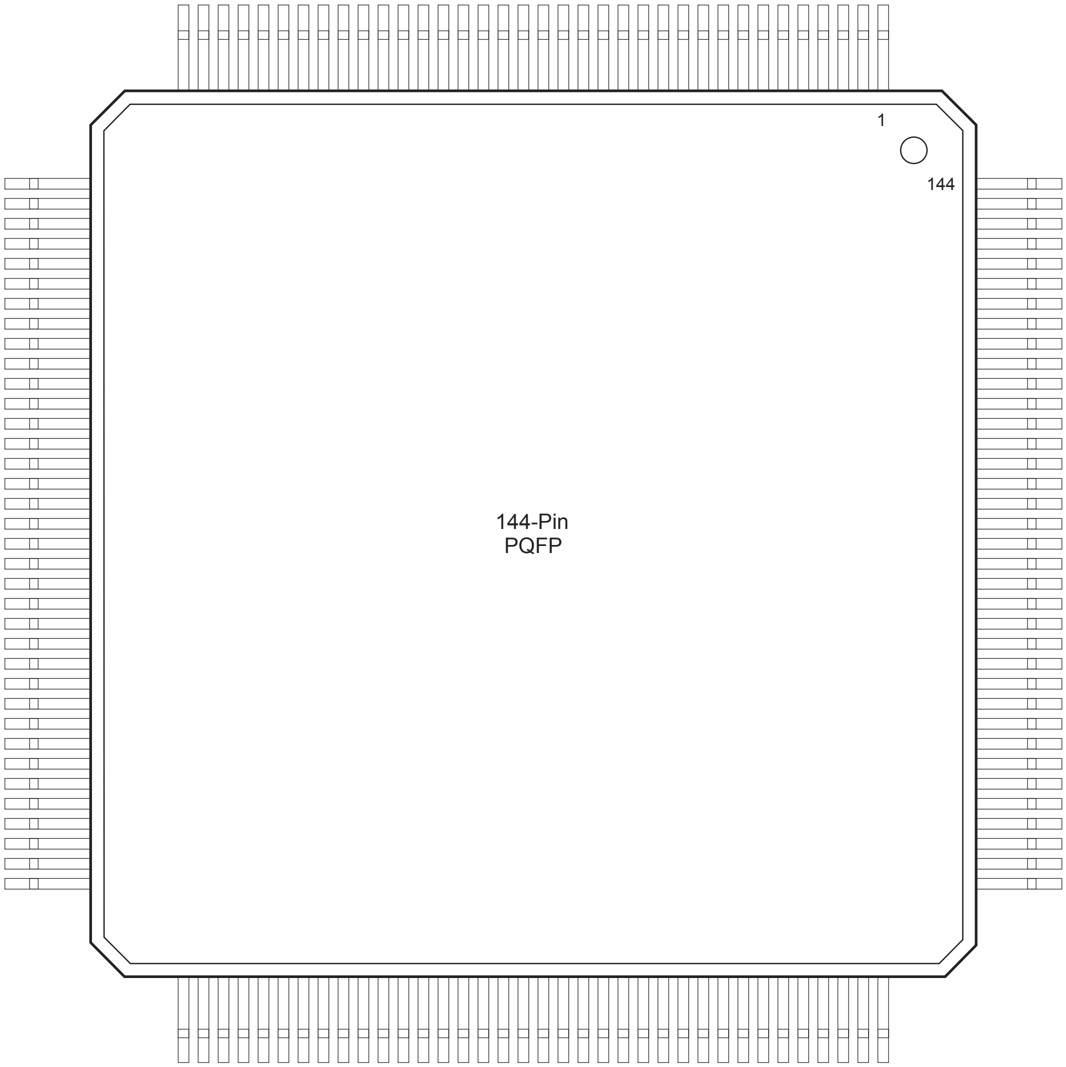
SDO Serial Data Output (Output)

Serial data output for diagnostic probe. SDO is active when the MODE pin is High. This pin functions as an I/O when the MODE pin is Low.

VCC 5.0 V Supply Voltage

High supply voltage.

PQ144



Note

For Package Manufacturing and Environmental information, visit the Resource Center at
http://www.microsemi.com/soc/products/solutions/package/docs.aspx

PQ144	
Pin Number	**A1240A Function**
2	MODE
9	GND
10	GND
11	GND
18	VCC
19	VCC
20	VCC
21	VCC
28	GND
29	GND
30	GND
44	GND
45	GND
46	GND
54	VCC
55	VCC
56	VCC
64	GND
65	GND
71	SDO
79	GND
80	GND
81	GND
88	GND

PQ144	
Pin Number	**A1240A Function**
89	VCC
90	VCC
91	VCC
92	VCC
93	VCC
100	GND
101	GND
102	GND
110	SDI, I/O
116	GND
117	GND
118	GND
123	PRA, I/O
125	CLKA, I/O
126	VCC
127	VCC
128	VCC
130	CLKB, I/O
132	PRB, I/O
136	GND
137	GND
138	GND
144	DCLK, I/O

Notes:

1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

PQ160	
Pin Number	**A1280A Function**
2	DCLK, I/O
6	VCC
11	GND
16	PRB, I/O
18	CLKB, I/O
20	VCC
21	CLKA, I/O
23	PRA, I/O
30	GND
35	VCC
38	SDI, I/O
40	GND
44	GND
49	GND
54	VCC
57	VCC
58	VCC
59	GND
60	VCC
61	GND
64	GND

PQ160	
Pin Number	**A1280A Function**
69	GND
80	GND
82	SDO
86	VCC
89	GN
98	GND
99	GND
109	GND
114	VCC
120	GND
125	GND
130	GND
135	VCC
138	VCC
139	VCC
140	GND
145	GND
150	VCC
155	GND
159	MODE
160	GND

Notes:

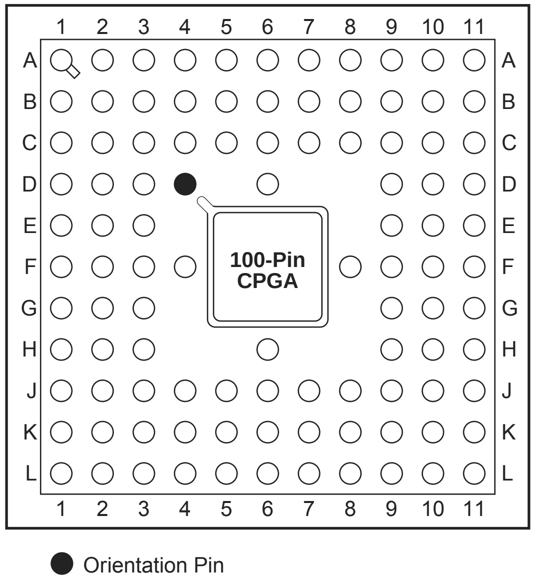
1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

TQ176		
Pin Number	**A1240A Function**	**A1280A Function**
155	VCC	VCC
156	GND	GND
158	CLKB, I/O	CLKB, I/O
160	PRB, I/O	PRB, I/O
161	NC	I/O
165	NC	NC
166	NC	I/O
168	NC	I/O
170	NC	VCC
173	NC	I/O
175	DCLK, I/O	DCLK, I/O

Notes:

1. NC denotes no connection.
2. All unlisted pin numbers are user I/Os.
3. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

PG100



Note

For Package Manufacturing and Environmental information, visit the Resource Center at
http://www.microsemi.com/soc/products/solutions/package/docs.aspx

PG100	
Pin Number	**A1225A Function**
A4	PRB, I/O
A7	PRA, I/O
B6	VCC
C2	MODE
C3	DCLK, I/O
C5	GND
C6	CLKA, I/O
C7	GND
C8	SDI, I/O
D6	CLKB, I/O
D10	GND
E3	GND

PG100	
Pin Number	**A1225A Function**
E11	VCC
F3	VCC
F9	VCC
F10	VCC
F11	GND
G1	VCC
G3	GND
G9	GND
J5	GND
J7	GND
J9	SDO
K6	VCC

Notes:

1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

PG132	
Pin Number	**A1240A Function**
A1	MODE
B5	GND
B6	CLKB, I/O
B7	CLKA, I/O
B8	PRA, I/O
B9	GND
B12	SDI, I/O
C3	DCLK, I/O
C5	GND
C6	PRB, I/O
C7	VCC
C9	GND
D7	VCC
E3	GND
E11	GND
E12	GND
F4	GND
G2	VCC

PG132	
Pin Number	**A1240A Function**
G3	VCC
G4	VCC
G10	VCC
G11	VCC
G12	VCC
G13	VCC
H13	GND
J2	GND
J3	GND
J11	GND
K7	VCC
K12	GND
L5	GND
L7	VCC
L9	GND
M9	GND
N12	SDO

Notes:

1. All unlisted pin numbers are user I/Os.
2. MODE pin should be terminated to GND through a 10K resistor to enable Actionprobe usage; otherwise it can be terminated directly to GND.

4 – Datasheet Information

List of Changes

The following table lists critical changes that were made in each version of the datasheet.

Revision	Changes	Page
Revision 8 (January 2012)	The ACT 2 datasheet was formatted newly in the style used for current datasheets. The same information is present (other than noted in the list of changes for this revision) but divided into chapters.	N/A
	Package names used in Table 1 • ACT 2 Product Family Profile and throughout the document were revised to match standards given in *Package Mechanical Drawings* (SAR 27395).	I
	The description for SDO pins had earlier been removed from the datasheet and has now been included again, in the "Pin Descriptions" section (SAR 35819).	2-21
	SDO pin numbers had earlier been removed from package pin assignment tables in the datasheet, and have now been restored to the pin tables (SAR 35819).	3-2
Revision 7 (June 2006)	The "Ordering Information" section was revised to include RoHS information.	II
Revision 6 (December 2000)	In the "PG176" package, pin A3 was incorrectly assigned as CLKA, I/O. A3 is a user I/O. Pin A9 is CLKA, I/O.	3-21

Microsemi

Microsemi Corporate Headquarters
One Enterprise, Aliso Viejo CA 92656 USA
Within the USA: +1 (949) 380-6100
Sales: +1 (949) 380-6136
Fax: +1 (949) 215-4996

Microsemi Corporation (NASDAQ: MSCC) offers a comprehensive portfolio of semiconductor solutions for: aerospace, defense and security; enterprise and communications; and industrial and alternative energy markets. Products include high-performance, high-reliability analog and RF devices, mixed signal and RF integrated circuits, customizable SoCs, FPGAs, and complete subsystems. Microsemi is headquartered in Aliso Viejo, Calif. Learn more at **www.microsemi.com**.

5172104-8/1.12